IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Original): A silicon-cobalt film forming composition which comprises a silicon compound and a cobalt compound.

Claim 2 (Original): The composition of claim 1, wherein the silicon compound is at least one compound selected from the group consisting of compounds represented by the following formulae (1a) to (1d):

$$Si_iX_{2i+2}$$
 (1a)

(wherein X is a hydrogen atom, a halogen atom or a monovalent organic group, and i is an integer of 2 or larger),

$$Si_jX_{2j}$$
 (1b)

(wherein X is a hydrogen atom, a halogen atom or a monovalent organic group, and j is an integer of 3 or larger),

$$Si_mX_{2m-2}$$
 (1c)

(wherein X is a hydrogen atom, a halogen atom or a monovalent organic group, and m is an integer of 4 or larger),

$$Si_kX_k$$
 (1d)

(wherein X is a hydrogen atom, a halogen atom or a monovalent organic group, and k is 6, 8 or 10).

Claim 3 (Currently Amended): The composition of claim 1 er 2, wherein the cobalt compound is a cobalt complex having at least either one of a CO ligand or a π ligand.

288992US0PCT Preliminary Amendment

Claim 4 (Currently Amended): A method for forming a silicon-cobalt film which comprises the steps of forming a coating film of the silicon-cobalt film forming composition of any of claims 1 to 3 claim 1 on a substrate and subjecting the film to a heat treatment and/or a light treatment.

Claim 5 (Original): A silicon-cobalt film formed by the method of claim 4.